

N-CHANNEL MOS FIELD EFFECT POWER TRANSISTOR

2SK797

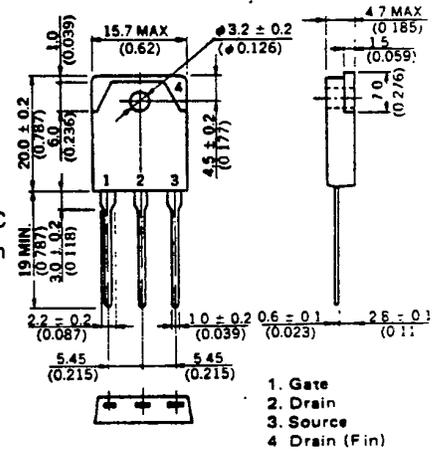
DESCRIPTION The 2SK797 is N-Channel MOS Field Effect Power Transistor designed for solenoid, motor and lamp driver.

- FEATURES**
- Gate Drive — Logic level —
 - Low $R_{DS(on)}$
 - No Secondary Breakdown

ABSOLUTE MAXIMUM RATINGS

- Maximum Temperatures**
- Storage Temperature -55 to +150 °C
 - Channel Temperature 150 °C Maximum
- Maximum Power Dissipations**
- Total Power Dissipation ($T_a = 25\text{ °C}$) 3.0 W
 - Total Power Dissipation ($T_c = 25\text{ °C}$) 150 W
- Maximum Voltages and Currents ($T_a = 25\text{ °C}$)**
- V_{DSS} Drain to Source Voltage 60 V
 - V_{GSS} Gate to Source Voltage ±20 V
 - $I_{D(DC)}$ Drain Current (DC) ±40 A
 - $I_{D(pulse)}$ Drain Current (pulse)* ±160 A
- * $PW \leq 300\ \mu s$, Duty Cycle $\leq 2\%$

PACKAGE DIMENSIONS
 in millimeters (inches)

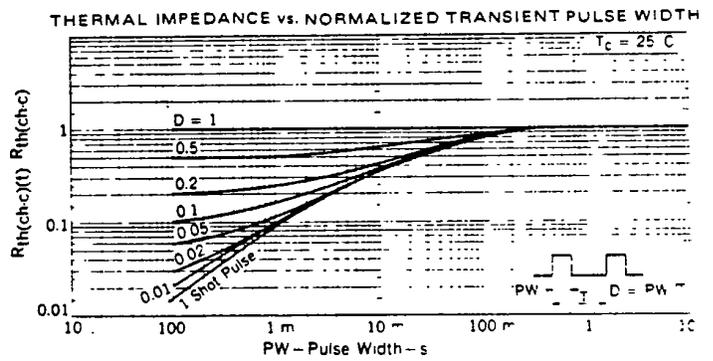
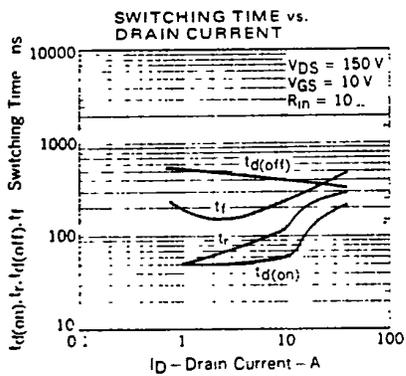
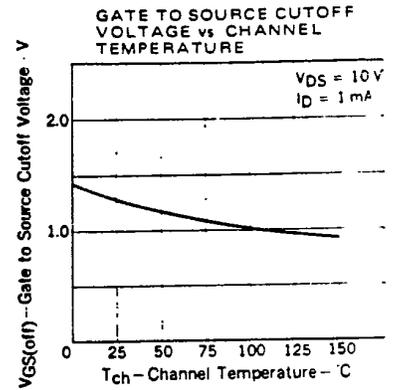
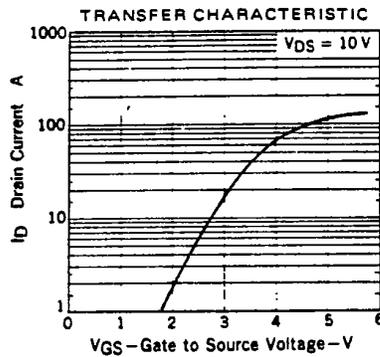
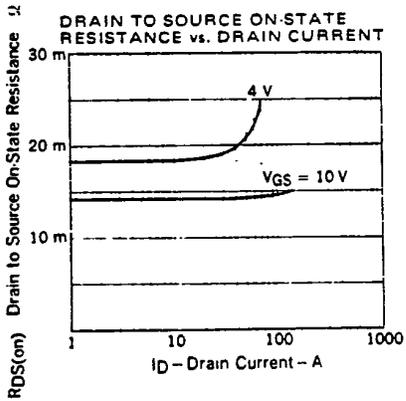


ELECTRICAL CHARACTERISTICS ($T_a = 25\text{ °C}$)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX	UNIT	TEST CONDITIONS
$R_{DS(on)}$	Drain to Source On-State Resistance			18	mΩ	$V_{GS} = 10\text{ V}$, $I_D = 20\text{ A}$
$R_{DS(on)}$	Drain to Source On-State Resistance			22	mΩ	$V_{GS} = 4\text{ V}$, $I_D = 20\text{ A}$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	1.0		2.5	V	$V_{DS} = 10\text{ V}$, $I_D = 1\text{ mA}$
$ Y_{fs} $	Forward Transfer Admittance	5.0			S	$V_{DS} = 10\text{ V}$, $I_D = 20\text{ A}$
I_{DSS}	Drain Leakage Current			100	μA	$V_{DS} = 60\text{ V}$, $V_{GS} = 0$
I_{GSS}	Gate to Source Leakage Current			±100	nA	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0$
C_{iss}	Input Capacitance		8000		pF	$V_{DS} = 10\text{ V}$ $V_{GS} = 0$ $f = 1\text{ MHz}$
C_{oss}	Output Capacitance		2400		pF	
C_{rss}	Reverse Transfer Capacitance		700		pF	
$t_{d(on)}$	Turn-On Delay Time		60		ns	
t_r	Rise Time		120		ns	$I_D = 20\text{ A}$, $V_{CC} = 50\text{ V}$ $R_L = 2.5\ \Omega$ $R_{in} = 10\ \Omega$
$t_{d(off)}$	Turn-Off Delay Time		400		ns	
t_f	Fall Time		250		ns	

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U.S.P. T. 4,145,115



SWITCHING TIME TEST CIRCUIT

